



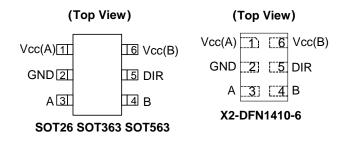
SINGLE BIT DUAL POWER SUPPLY TRANSLATING TRANSCEIVER WITH 3 STATE OUTPUTS

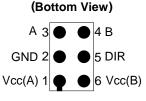
Description

The 74LVC1T45 is a single-bit, dual-supply transceiver with tri-state outputs suitable for transmitting a single logic bit across different voltage domains. The A input/output pin is designed to track V_{CCA} while the B input/output tracks V_{CCB} . This arrangement allows for universal low-voltage translation between any voltages from 1.65V to 5.5V. The Direction pin (DIR) controls the direction of the transceiver and in a logic voltage related to V_{CCA} . When a high logic level is applied to DIR, the A pin becomes an input, and the B pin becomes the output. Conversely, the roles of A and B are reversed when DIR is asserted low.

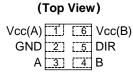
The tri-state feature occurs when either of the power supply voltages are zero. This is also an loff feature and allows for the output to remain in a high impedance state with both power supplies at 0V, which prevents and damages backflow currents and provides power-down electrical isolation up to 5.5V as not to interfere with any logic activity on pin A or B.

Pin Assignments









X2-DFN1010-6

Features

- Wide Supply Voltage Range:
 - V_{CC}(A): from 1.65V to 5.5V
 - V_{CC}(B): from 1.65V to 5.5V
- ± 24mA Output Drive at 3.3V
- CMOS Low Power Consumption 16µA Maximum I_{CC}
- High Noise Immunity—(100mV Hysteresis Typical)
- IOFF Supports Partial-Power-Down Mode Operation
- I_{OFF} Controlled by Either V_{CC} Being at 0 V
- Inputs Accept up to 5.5V
- ESD Protection Exceeds JESD 22
 - 200-V Machine Model (A115)
 - 2000-V Human Body Model (A114)
 - 1000 V Charged Device Model (C101)
- Latch-up Exceeds 100mA per JESD 78, Class I
- X2-DFN1409-6 Package Designed as a Direct Replacement for Chip Scale Packaging.
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Applications

- Voltage Level Translation
 Well-Suited to Join Logic Types Operating at Different Voltages
- Power-Down Signal Isolation

 If Either Voltage Domain is Turned Off the Signal is Isolated and
 There is No Loading on Signal Lines
- Wide Array of Products, such as:
 - Cell Phones, Tablets, E-Readers
 - PCs, Notebooks, Netbooks, Ultrabooks
 - Networking, Routers, Gateways
 - Computer Peripherals, Hard Drives, CD/DVD ROM
 - TV, DVD, DVR, Set-Top Box
 - Personal Navigation / GPS
 - MP3 Players, Cameras, Video Recorders

Notes:

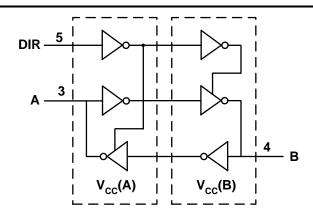
- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Pin Descriptions

Pin Name	Pin	Function
VCC(A)	1	Supply for I/O Pin A; Reference for DIR
GND	2	Ground
А	3	Data Input/Output
В	4	Data Input/Output
DIR	5	Direction Control
VCC(B)	6	Supply for I/O Pin B

Logic Diagram



Function Tables

Input DIR (Direction Pin)	Operation
L	B Data to A Output
Н	A Data to B Output

	Inputs		Outp	outs
Α	В	DIR	Α	В
Note 4	L	L	L	Note 4
Note 4	Н	L	Н	Note 4
L	Note 4	Н	Note 4	L
Н	Note 4	Н	Note 4	Н

Note:

Absolute Maximum Ratings (Note 5) (@T_A = +25°C, unless otherwise specified.)

Symbol	Parameter		Rating	Unit			
ESD HBM	Human Body Model ESD Protection	· · · · · · · · · · · · · · · · · · ·					
ESD CDM	Charged Device Model ESD Protection	1	KV				
ESD MM	Machine Model ESD Protection	200	V				
Vcc(A), Vcc(B)	Supply Voltage Range	-0.5 to +6.5	V				
VI	Input Voltage Range						
Vo	Voltage Applied to Output in High Impedance or IOFF	Itage Applied to Output in High Impedance or I _{OFF} State					
.,,	Valtage Applied to Output in High and any Otate	A Pin	-0.3 to V _{CC} (A) +0.5	V			
Vo	Voltage Applied to Output in High or Low State	B Pin	-0.3 to V _{CC} (B) +0.5	V			
I _{IK}	Input Clamp Current V _I <0		-50	mA			
lok	Output Clamp Current		-50	mA			
Io	Continuous Output Current		±50	mA			
_	Continuous Current Through Vcc or GND		±100	mA			
TJ	Operating Junction Temperature		-40 to +150	°C			
T _{STG}	Storage Temperature		-65 to +150	°C			

Note:

^{4.} Pin condition not applicable as defined by DIR.

^{5.} Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.



Recommended Operating Conditions (Note 6) (@T_A = +25°C, unless otherwise specified.)

Symbol		Parameter	V _{CC} Inputs	V _{CC} Outputs	Min	Max	Units
V _{CC} (A)	On a nation of 1/alt		_	_	1.65	5.5	V
V _{CC} (B)	Operating Volt	age	_	_	1.65	5.5	V
			$V_{CC} = 1.65V \text{ to } 1.95V$	_	0.65 X V _{CC(A)}	_	
.,	High-Level Inp	ut Voltage Pin A or DIR	$V_{CC} = 2.3V \text{ to } 2.7V$	_	1.7	_	
V _{IH}	Referenced to	V _{CC} (A)	$V_{CC} = 3V \text{ to } 3.6V$	_	2	_	V
			$V_{CC} = 4.5V \text{ to } 5.5V$	_	0.7 X V _{CC(A)}	_	
			$V_{CC} = 1.65V \text{ to } 1.95V$	_		0.35 X V _{CC(A)}	
.,	Low-Level Inpu	ut Voltage Pin A or DIR	$V_{CC} = 2.3V \text{ to } 2.7V$	_	_	0.7	
V_{IL}	Referenced to	V _{CC} (A)	$V_{CC} = 3V \text{ to } 3.6V$	_	_	0.8	V
			$V_{CC} = 4.5V \text{ to } 5.5V$	_	_	0.3 X V _{CC(A)}	
			V _{CC} = 1.65V to 1.95V	_	0.65 X V _{CC(B)}	_	
V	High-Level Inp	ut Voltage Pin B Referenced to	$V_{CC} = 2.3V \text{ to } 2.7V$	_	1.7	_	
V _{IH}	V _{CC} (B)		$V_{CC} = 3V \text{ to } 3.6V$	_	2	_	V
			$V_{CC} = 4.5V \text{ to } 5.5V$	_	0.7 X V _{CC(B)}	_	
			V _{CC} = 1.65V to 1.95V	_	_	0.35 X V _{CC(B)}	
.,	Low-Level Inpu	ut Voltage Pin B Referenced to	$V_{CC} = 2.3V \text{ to } 2.7V$	_	_	0.7	
V_{IL}	V _{CC} (B)		$V_{CC} = 3V \text{ to } 3.6V$	_	_	0.8	V
			$V_{CC} = 4.5V \text{ to } 5.5V$	_	_	0.3 X V _{CC(B)}	
VI	Input Voltage		_	_	0	5.5	V
Vo	Output Voltage)	_	_	0	V _{CC}	V
			_	$V_{CC} = 1.65V \text{ to } 1.95V$		-4	
	Libert Lavel Ove	to at Carrent	_	$V_{CC} = 2.3V \text{ to } 2.7V$		-8	A
Іон	High-Level Ou	tput Current	_	V _{CC} = 3V to 3.6V		-24	mA
			_	$V_{CC} = 4.5V \text{ to } 5.5V$		-32	
			_	$V_{CC} = 1.65V \text{ to } 1.95V$		4	
	l avvil avval Ovit	must Cummant	_	$V_{CC} = 2.3V \text{ to } 2.7V$		8	A
l _{OL}	Low-Level Out	put Current	_	V _{CC} = 3V to 3.6V		24	mA
			_	$V_{CC} = 4.5V \text{ to } 5.5V$		32	
			V _{CC} = 1.65V to 1.95V	_	-	20	
	Input	Deta Innuta	$V_{CC} = 2.3V \text{ to } 2.7V$		I	20	
Δt/ΔV	Transition	Data Inputs	V _{CC} = 3V to 3.6V			10	ns/V
	Rise or Fall Rate		V _{CC} = 4.5V to 5.5V	_	-	5	
	i vaic	Control Inputs		_	_	5	
T _A	Operating Free	e-Air Temperature	_	_	-40	+125	°C

Note:

6. Unused inputs should be held at $\ensuremath{V_{\text{CC}}}$ or Ground.



Electrical Characteristics (@T_A = +40°C to +85°C, unless otherwise specified.)

Come !	Danas	-	. Conditions	V (A)	\/ (D)	Т	_A = +25°	C	T _A = -40°C	to +85°C	
Symbol	Parameter	Tes	t Conditions	V _{CC} (A)	V _{CC} (B)	Min	Тур	Max	Min	Max	Unit
		I _{OH} = -100	μA	1.65V to 5.5V	1.65V to 5.5V	_		_	V _{CC} – 0.1	_	
		I _{OH} = -4m/	4	1.65V	1.65V	_	_	_	1.2	_	
V _{OH}	High Level Output	I _{OH} = -8m/	Α	2.3V	2.3V	_	_	_	1.9	_	٧
	Voltage	I _{OH} = -24n	nΑ	3V	3V	_	_	_	2.4	_	
		$I_{OH} = -32n$	nΑ	4.5V	4.5V	_	_	_	3.8		
		I _{OL} = 100μA		1.65V to 5.5V	1.65V to 5.5V	_	_	_	_	0.1	
		$I_{OL} = 4mA$		1.65V	1.65V	_		_	_	0.45	
VoL	Low-Level Output Voltage	$I_{OL} = 8mA$		2.3V	2.3V	_	_	_	_	0.3	٧
	Voltage	$I_{OL} = 8 \text{ mA}$ $I_{OL} = 24 \text{ mA}$		3V	3V	_		_	_	0.55	
		$I_{OL} = 32m$	A	4.5V	4.5V	_		_	_	0.55	
II	Input Current	DIR	$V_I = V_{CC}(A)$ or GND	0 to 5.5V	0 to 5.5V	_	_	± 1		±2	μΑ
l _{OFF}	Power Down	A Pin	V_I or $V_O = 0$ to	0	0V to 5.5V	_	_	± 1	_	±2	μA
011	Leakage Current	B Pin 5.5V		0 to 5.5V	0	_	_	± 1	_	±2	F
	3-State Leakage	A Pin $V_O = V_{CC}(A)$		1.65V to 5.5V	1.65V to 5.5V	_	_	± 1	_	±2	
l _{OZ}	Current	B Pin $V_O = V_{CC}(B)$		1.65V to 5.5V	1.65V to 5.5V	_	_	± 1	_	±2	μA
		\	CND	1.65V to 5.5V	1.65V to 5.5V	_	_	_	_	3	
Icca	Supply Current	$V_1 = 5.5V_1$	or GND	5.5V	0	_		_	_	2	μΑ
		$I_O = 0$		0	5.5V	_		_	_	-2	
		V _I = 5.5V	or CND	1.65V to 5.5V	1.65V to 5.5V	_	_	_	_	3	
I _{CCB}	Supply Current	$I_0 = 0$	OI GIND	0V	5.5V	_	_	_	_	2	μΑ
		10 = 0		5.5V	0V	_	_	_	_	-2	
I _{CCA} +	Supply Current	V _I = 5.5V	or GND I _O = 0	1.65V to 5.5V	1.65V to 5.5V	_	_	_	_	4	μΑ
ΔI _{CCA}	Additional Supply	A Pin	$A = V_{CC}(A) - 0.6V$ $DIR = V_{CC}(A)$ $B = Open$	3V to 5.5V	3V to 5.5V					50	μA
ДІССА	Current	DIR= $V_{CC}(A)$ -0.6V A= $V_{CC}(A)$ or GND B = Open		37 10 3.37	37 10 3.37					50	μ
ΔI _{CCB}	Additional Supply Current	$B = V_{CC}(B) -0.6V$ $DIR = GND$ $A = Open$		3V to 5.5V	3V to 5.5V	_	_	_	_	50	μΑ
Cı	Input Capacitance	II)IR I	V _I = V _{CC} (A) or GND	3.3V	3.3V		2.5		_	_	pF
C _{IO}	Input/Output Capacitance	1	$V_i = V_{CC}(A)/(B)$ or GND	3.3V	3.3V	_	6.0	_	_	_	pF



Electrical Characteristics (@T_A = +40°C to +125°C, unless otherwise specified.)

Symbol	Parameter	Toe	t Conditions	V _{CC} (A)	V _{CC} (B)	T _A = -40°C	to +125°C	Unit
Зуппоп	Farameter	162	Test Conditions OH = -100µA		ACC(P)	Min	Max	Onic
		I _{OH} = -100μA		1.65V to 5.5V	1.65V to 5.5V	V _{CC} – 0.1	_	
		I _{OH} = -4mA		1.65V	1.65V	1.2	_	
V_{OH}	High Level	$I_{OH} = -8mA$		2.3V	2.3V	1.9	_	V
	Output Voltage	I _{OH} = -24mA		3V	3V	2.4	_	
		I _{OH} = -32mA		4.5V	4.5V	3.8	_	
		I _{OL} = 100μA		1.65V to 5.5V	1.65V to 5.5V	_	0.1	
		I _{OL} = 4mA			1.65V	_	0.45	
V_{OL}	High-Level Input	I _{OL} = 8mA		2.3V	2.3V	_	0.3	V
	Voltage	$I_{OL} = 24\text{mA}$		3V	3V	_	0.55	
		I _{OL} = 32mA			4.5V	_	0.55	
II	Input Current	DIR	$V_I = V_{CC}(A)$ or GND	0 to 5.5V	0 to 5.5V	_	± 2	μA
l _{OFF}	Power Down Leakage	A Pin	V_1 or $V_0 = 0$ to 5.5V	0	1.65V to 5.5V	_	± 2	μΑ
OFF	Current	B Pin	V C V V C V C V C V C V C V C V C V C V	1.65V to 5.5V	0V	_	± 2	μΛ
loz	3-State Leakage	B Pin $V_O = V_{CC}(B)$ DIR = 0 V	V _I = 0 to 5.5V	1.65V to 5.5V	1.65V to 5.5V	_	±2	μА
	Current	A Pin $V_O = V_{CC}(A)$ DIR= $V_{cc}(A)$		1.65V to 5.5V	1.65V to 5.5V	_	± 2	·
		V _I = 5.5V or GN	ID	1.65V to 5.5V	1.65V to 5.5V		3	
I _{CCA}	Supply Current	$I_0 = 0$	ND	5.5V	0		2	μΑ
		10 = 0		0	5.5V	_	-2	
		V _I = 5.5V or GN	ID	1.65V to 5.5V	1.65V to 5.5V	_	3	
I _{CCB}	Supply Current	$I_0 = 0$	ND	5.5V	0	_	2	μΑ
		10 = 0		0	5.5V	_	-2	
I _{CCA} + I _{CCB}	Supply Current	$V_I = 5.5V$ or GN $I_O = 0$	ND	1.65V to 5.5V	1.65V to 5.5V	_	4	μA
	Additional	A Pin	$A = V_{CC}(A) -0.6V$ $DIR = V_{CC}(A)$ $B = Open$	2)/4: 5 5)/	2)/4-5-51/		50	
ΔI _{CCA}	Supply Current	DIR	DIR= V_{CC} (A) -0.6V A= V_{CC} (A) or GND B = Open	3V to 5.5V	3V to 5.5V	_	50	μA
ΔI_{CCB}	Additional Supply Current	B Pin	$B = V_{CC}(B) - 0.6V$ DIR = GND A = Open	3V to 5.5V	3V to 5.5V	_	50	μA



$\label{eq:package Characteristics} \textbf{Package Characteristics} \ (\textbf{V}_{CC} = 3.3 \textbf{V}, \ \textbf{T}_{A} = +25 ^{\circ} \textbf{C}, \ \text{unless otherwise specified.})$

Symbol	Parameter	Package	Test Conditions	Min	Тур	Max	Unit
		SOT26		_	166	_	
		SOT363		_	371	_	
0	Thermal Resistance Junction-	SOT563	Note 7	_	290	_	°C/W
Θ_{JA}	to-Ambient	DFN1410	Note /	_	430	_	C/VV
		DFN1409		_	450	_	
		DFN1010		_	510	_	
		SOT26			46	_	
		SOT363		-	143	_	
	Thermal Resistance Junction-	SOT563	Note 7	_	96	_	°C/W
Өлс	to-Case	DFN1410	Note /	_	190	_	C/VV
		DFN1409			200	_	
	10	DFN1010		_	250	_	

Note:

Switching Characteristics (V_{CC} (A) = 1.8V \pm 0.15V, T_A = -40°C to +85°C, see Figure 1)

Parameter	From (Input)			= 1.8V 15V		= 2.5V .2V		= 3.3V .3V	V _{CC} (B)= 5V ±0.5V		Unit
	(iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pLH}	A	В	3	17.7	2.2	10.3	1.7	8.3	1.4	7.5	ns
t _{pHL}	A	В	2.8	14.3	2.2	8.5	1.8	8.1	1.7	7.5	115
t _{pLH}	В	А	3	17.7	2.3	16	2.1	15.5	1.9	15.1	no
t _{pHL}		_ ^	2.8	14.3	2.1	12.9	2	12.6	1.8	12.2	ns
t _{pHZ}	DIR	А	5.2	19.4	4.8	18.5	4.7	18.4	5.1	17.1	ns
t _{pLZ}	DIK	A	2.3	10.5	2.1	10.5	2.4	10.7	3.1	10.9	115
t _{pHZ}	DIR	В	6.4	21.9	4.9	11.5	4.6	10.3	2.8	8.2	no
t _{pLZ}	DIK	В	4.2	17	3.7	9.6	3.3	8.8	2.4	8.0	ns
t _{pZH}	DID	^	_	33.7	_	25.2	_	23.9	_	21.5	
t _{pZL}	DIR A	_	36.2	_	24.4	_	22.9	_	20.4	ns	
t _{pZH}	DIR	В	_	28.2	_	20.8	_	19	_	18.1	
t _{pZL}	DIK	В	_	33.7	_	27	_	25.5	_	24.1	ns

Switching Characteristics (continued) (V_{CC} (A) = 2.5V ± 0.2V, T_A = -40°C to +85°C, see Figure 1)

Parameter	From (Input)	To (Output)		= 1.8V 15V	V _{CC} (B) = 2.5V ±0.2V		V _{CC} (B) = 3.3V ±0.3V		V _{CC} (B) = 5V ±0.5V		Unit
	(iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pLH}	A	В	2.3	16	1.5	8.5	1.3	6.4	1.1	5.1	
t _{pHL}	A	В	2.1	12.9	1.4	7.5	1.3	5.4	0.9	4.6	ns
t _{pLH}	В	А	2.2	10.3	1.5	8.5	1.4	8	1	7.5	ns
t _{pHL}		_ ^	2.2	8.5	1.4	7.5	1.3	7	0.9	6.2	115
t _{pHZ}	DIR	^	3	8.1	3.1	8.1	2.8	8.1	3.2	8.1	
t _{pLZ}	DIK	Α	1.3	5.9	1.3	5.9	1.3	5.9	1	5.8	ns
t _{pHZ}	DIR	В	5.5	23.7	3.6	11.4	3.5	10.2	2.4	7.1	no
t _{pLZ}	DIK	В	3.9	18.9	3.2	9.6	2.8	8.4	1.8	5.3	ns
t _{pZH}	DIR	^	_	29.2	_	18.1	_	16.4	_	12.8	
t _{pZL}	DIK	Α	_	32.2	_	18.9	_	17.2	_	13.3	ns
t _{pZH}	DIR	В	_	21.9	_	14.4	_	12.3	_	10.9	ns

^{7.} Test condition for SOT26, SOT363, DFN1410, DFN1409 and DFN1010: Device mounted on FR-4 substrate PCB, 2oz copper with minimum recommended pad layout.



Switching Characteristics (continued) (V_{CC} (A) = 3.3V \pm 0.3V, T_{A} = -40°C to +85°C, see Figure 1)

Parameter	From (Input)	To (Output)		= 1.8V 15V		= 2.5V .2V		= 3.3V .3V		3) = 5V 5.5V	Unit
	(iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pLH}	A	В	2.1	15.5	1.4	8	0.7	5.8	0.7	4.4	200
t _{pHL}		В	2	12.6	1.3	7	0.8	5	0.7	4	ns
t _{pLH}	- В	А	1.7	8.3	1.3	6.4	0.7	5.8	0.6	5.4	no
t _{pHL}]	A	1.8	7.1	1.3	5.4	0.8	5	0.7	4.5	ns
t _{pHZ}	DIR	^	2.9	7.3	3	7.3	2.8	7.3	3.4	7.3	
t _{pLZ}	DIK	A	1.8	5.6	1.6	5.6	2.2	5.7	2.2	5.7	ns
t _{pHZ}	DIR	В	4.0	20.5	3.5	10.1	2.9	8.8	2.4	6.8	no
t _{pLZ}	DIR	В	3.3	14.5	2.9	7.8	2.4	7.1	1.7	4.9	ns
t _{pZH}	DID	^	_	22.8	_	14.2	_	12.9	_	10.3	
t _{pZL}	DIR A	_	27.6	_	15.5	_	13.8	_	11.3	ns	
t _{pZH}	DIR	В	_	21.1	_	13.6	_	11.5	_	10.1	no
t _{pZL}		В	_	19.9	_	14.3	_	12.3	_	11.3	ns

Switching Characteristics (continued) (V_{CC} (A) = 5V \pm 0.5V, T_A = -40°C to +85°C, see Figure 1)

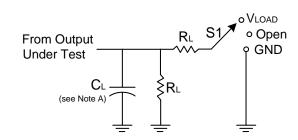
Parameter	From (Input)	To (Output)		= 1.8V 15V		= 2.5V .2V	V _{CC} (B) = 3.3V ±0.3V		V _{CC} (B)= 5V ±0.5V		Unit
	(iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pLH}	A	В	1.9	15.1	1	7.5	0.6	5.4	0.5	3.9	ns
t _{pHL}	7	B	1.8	12.2	0.9	6.2	0.7	4.5	0.5	3.5	115
t _{pLH}	В	А	1.4	8.5	1	5.1	0.7	4.4	0.5	3.9	
t _{pHL}]	A	1.7	8.5	0.9	4.6	0.7	4	0.5	3.5	ns
t _{pHZ}	DIR	А	2.1	5.4	2.2	5.4	2.2	5.5	2.2	5.4	
t _{pLZ}		^	0.9	3.8	1	3.8	1	3.7	0.9	3.7	ns
t _{pHZ}	DIR	В	4.8	20.2	2.5	9.8	1	8.5	2.2	6.5	
t _{pLZ}) DIK	В	4.2	14.8	2.5	7.4	2.5	7	1.6	4.5	ns
t _{pZH}	DIR	^	_	22	_	12.5	_	11.4	_	8.4	
t _{pZL}	אוט	Α	_	27.2	_	14.4	_	12.5	_	10	ns
t _{pZH}	DIR	В	_	18.9	_	11.3	_	9.1	_	7.6	ns

Operating Characteristics (T_A = +25°C, unless otherwise specified.)

Power Dis	Parameter sipation Capacitance	Test Conditions	V _{CC} (A) = V _{CC} (B) = 1.8V Typ	$V_{CC}(A) = V_{CC}(B) = 2.5V$ Typ	$V_{CC}(A) = V_{CC}(B) = 3.3V$ Typ	$V_{CC}(A) = V_{CC}(B) = 5V$ Typ	Unit
	A- Input, B- Output	$C_L = 0 pF$	3	4	4	4	
C _{pd} (A)	B- Input, A- Output	f = 10 MHz tr = tf = 1 ns	18	19	20	21	pF
	A- Input, B- Output	$C_L = 0 pF$	18	19	20	21	
C _{pd} (B)	B- Input, A- Output	f = 10 MHz tr = tf = 1 ns	3	4	4	4	pF

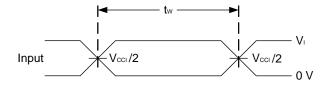


Parameter Measurement Information

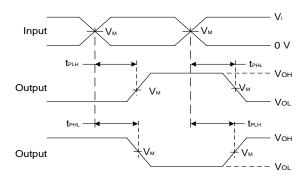


TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	Vload
t _{PHZ} /t _{PZH}	GND

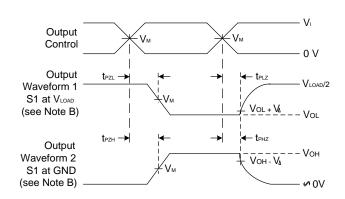
V	Inputs		V V	V		RL	V.
V _{CC}	VI	t _r /t _f	V _M	V_{LOAD}	CL	KL	V Δ
1.8V±0.15V	V _{CCI}	≤2ns	V _{CCO} /2	2 X V _{CCO}	15pF	2ΚΩ	0.15V
2.5V±0.2V	Vcc	≤2ns	V _{CCO} /2	2 X V _{CCO}	15pF	2ΚΩ	0.15V
3.3V±0.3V	3V	≤2.5ns	V _{CCO} /2	2 X V _{CCO}	15pF	2ΚΩ	0.3V
5V±0.5V	V _{CC}	≤2.5ns	V _{CCO} /2	2 X V _{CCO}	15pF	2ΚΩ	0.3V



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs



Voltage Waveform Enable and Disable Times Low and High Level Enabling

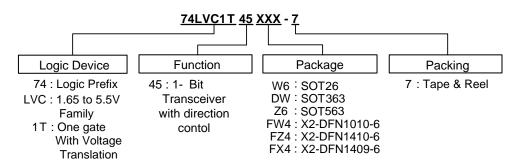
Figure 1 Load Circuit and Voltage Waveforms

Notes:

- 8. Includes test lead and test apparatus capacitance.
- Waveform 1 is for an output with input set up as a low and device coming out or into 3-state via DIR control.
 Waveform 2 is for an output with input set up as a high and device coming out or into 3-state via DIR control.
- 10. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
- 11. t_{PLZ} and t_{PHZ} are the same as $t_{\text{dis.}}$
- 12. t_{PZL} and t_{PZH} are the same as t_{EN}.
- 13. t_{PLH} and t_{PHL} are the same as $t_{PD.}$
- 14. V_{CCI} is the V_{CC} associated with the input.
- 15. V_{CCO} is the V_{CC} associated with the output.



Ordering Information

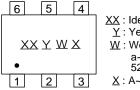


Part Number	Package Code Packaging	7" Tape and Reel (Note 7)		
Fait Number		Packaging	Quantity	Part Number Suffix
74LVC1T45W6-7	W6	SOT26	3000/Tape & Reel	-7
74LVC1T45DW-7	DW	SOT363	3000/Tape & Reel	-7
74LVC1T45Z6-7	Z6	SOT563	4000/Tape & Reel	-7
74LVC1T45FW4-7	FW4	X2-DFN1010-6	5000/Tape & Reel	-7
74LVC1T45FZ4-7	FZ4	X2-DFN1410-6	5000/Tape & Reel	-7
74LVC1T45FX4-7	FX4	X2-DFN1409-6	5000/Tape & Reel	-7

Note: 16. The taping orientation is located on our website at http://www.diodes.com/package-outlines.html.

Marking Information

(1) SOT363, SOT563



XX: Identification code

Y : Year 0~9

W: Week: A~Z: 1~26 week;

a~z: 27~52 week; z represents 52 and 53 week

X: A~Z: Internal Code

Part Number	Package	Identification Code
74LVC1T45W6	SOT26	TT
74LVC1T45DW	SOT363	TR
74LVC1T45Z6	SOT563	TS

(2) X2-DFN1010-6, X2-DFN1410-6, and X2-DFN1409-6

(Top View)

 $\frac{XX}{Y}$: Identification Code $\frac{X}{Y}$: Year • $0 \sim 0$

W: Week: A~Z: 1~26 week; a~z: 27~52 week; z represents

52 and 53 week X: A~Z: Internal code

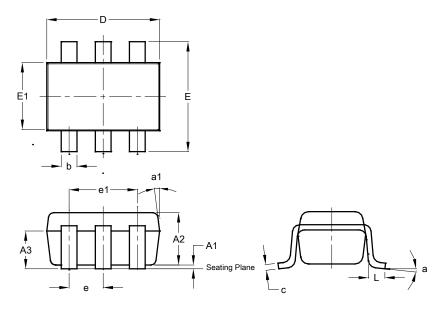
Part Number	Package	Identification Code
74LVC1T45FW4	X2-DFN1010-6	TR
74LVC1T45FX4	X2-DFN1409-6	TT
74LVC1T45FZ4	X2-DFN1410-6	TS



Package Outline Dimensions (All dimensions in mm.)

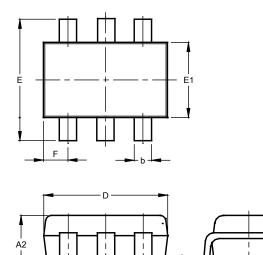
Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) Package Type: SOT26



;	SOT26 (SC74R)					
Dim	Min	Max	Тур			
A1	0.013	0.10	0.05			
A2	1.00	1.30	1.10			
A3	0.70	0.80	0.75			
b	0.35	0.50	0.38			
С	0.10	0.20	0.15			
D	2.90	3.10	3.00			
е	_		0.95			
e1	_		1.90			
Е	2.70	3.00	2.80			
E1	1.50	1.70	1.60			
L	0.35	0.55	0.40			
а			8°			
a1			7°			
All Dimensions in mm						

(2) Package Type: SOT363



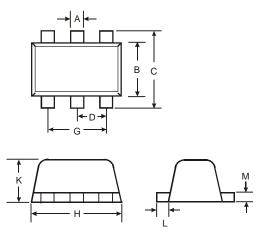
	SOT363					
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.90	1.00	0.95			
b	0.10	0.30	0.25			
С	0.10	0.22	0.11			
D	1.80	2.20	2.15			
Е	2.00	2.20	2.10			
E1	1.15	1.35	1.30			
е	C	.650 E	SC			
F	0.40	0.45	0.425			
L	0.25	0.40	0.30			
а	0°	8°	_			
All I	Dimen	sions	in mm			



Package Outline Dimensions (All dimensions in mm.)

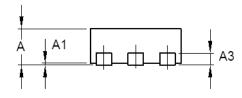
Please see http://www.diodes.com/package-outlines.html for the latest version.

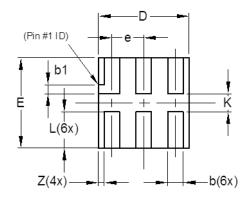
(3) Package Type: SOT563



SOT563					
Dim	Min	Max	Тур		
Α	0.15	0.30	0.20		
В	1.10	1.25	1.20		
С	1.55	1.70	1.60		
D	_	_	0.50		
G	0.90	1.10	1.00		
Н	1.50	1.70	1.60		
K	0.55	0.60	0.60		
L	0.10	0.30	0.20		
М	0.10	0.18	0.11		
All	Dimens	sions in	mm		

(4) Package Type X2-DFN1010-6





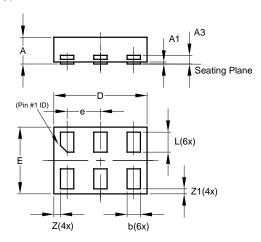
X2-DFN1010-6					
Dim	Min	Max	Тур		
Α	_	0.40	0.39		
A 1	0.00	0.05	0.02		
А3			0.13		
b	0.14	0.20	0.17		
b1	0.05	0.15	0.10		
D	0.95	1.05	1.00		
Е	0.95	1.05	1.00		
е	_	_	0.35		
L	0.35	0.45	0.40		
K	0.15	_	_		
Z	_	_	0.065		
All Dimensions in mm					



Package Outline Dimensions (All dimensions in mm.)

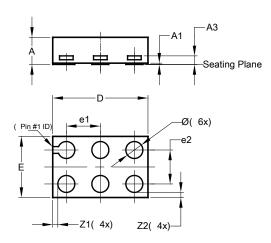
Please see http://www.diodes.com/package-outlines.html for the latest version.

(5) Package Type: X2-DFN1410-6



X2-DFN1410-6					
Dim	Min	Max	Тур		
Α	_	0.40	0.39		
A1	0.00	0.05	0.02		
A3	_	_	0.13		
b	0.15	0.25	0.20		
D	1.35	1.45	1.40		
Е	0.95	1.05	1.00		
е	_	_	0.50		
L	0.25	0.35	0.30		
Ζ	_	_	0.10		
Z 1	0.045	0.105	0.075		
All Dimensions in mm					

(6) Package Type: X2-DFN1409-6



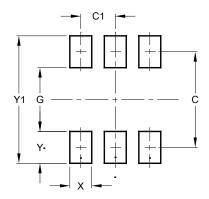
X2-DFN1409-6					
Dim	Min	Max	Тур		
Α	-	0.40	0.39		
A1	0	0.05	0.02		
A3	-	ı	0.13		
Ø	0.20	0.30	0.25		
D	1.35	1.45	1.40		
Е	0.85	0.95	0.90		
e1	-	-	0.50		
e2	1	-	0.50		
Z 1	-	ı	0.075		
Z2	-	-	0.075		
All Dimensions in mm					



Suggested Pad Layout

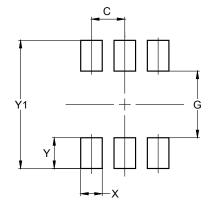
Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) Package Type: SOT26



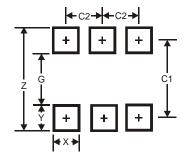
Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Y	0.80
Y1	3.20

(2) Package Type: SOT363



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Υ	0.600
Y1	2.500

(3) Package Type: SOT563



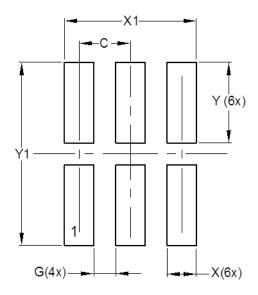
Dimensions	SOT563
Z	2.2
G	1.2
X	0.375
Υ	0.5
C1	1.7
C2	0.5



Suggested Pad Layout

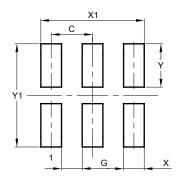
Please see http://www.diodes.com/package-outlines.html for the latest version.

(4) Package Type X2-DFN1010-6



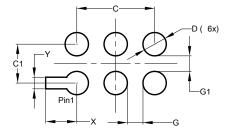
Dimensions	Value (in mm)
С	0.350
G	0.150
X	0.200
X1	0.900
Y	0.550
Y1	1.250

(5) Package Type: X2-DFN1410-6



Dimension	Value
s	(in mm)
С	0.500
G	0.250
Х	0.250
X1	1.250
Y	0.525
Y1	1 250

(6) Package Type: X2-DFN1409-6



Dimensions	Value (in mm)
С	1.000
C1	0.500
D	0.300
G	0.200
G1	0.200
X	0.400
Y	0.150



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2018, Diodes Incorporated

www.diodes.com